

EAST - [10671473.wpp.1]

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Pending
Active
19: (13) (((memory and redundan\$2) and ((defect\$3 adj3 address) and defect\$3 near3 stor\$3)) and (redundan\$2 adj2 decoder)) and (subblock sub-block)) and (defect\$3 near3 stor\$3 near3 circuit)]

Failed
Saved
(96) (shift adj2 redundan\$4) and defect\$3 and memory
(40) (shift adj2 redundan\$4) and (defect\$3 adj3 (line bus connect
(30) (shift adj2 redundan\$4) and (defect\$3 adj3 line) and memory
(1) ((shift adj2 redundan\$4) and (defect\$3 adj3 (line bus connect
(10) ((shift adj2 redundan\$4) and (defect\$3 adj3 (line bus connect
(12) ((shift adj2 redundan\$4) and (defect\$3 adj3 (line bus connect
(47149) address near2 input
(8) (US-6314033-S or US-6188597-S or US-5491655-S or US-6304501-S
(1) L63 and L64
(5) (address near2 input) and ((US-6314033-S or US-6188597-S or US-
(1880) (address near3 input) and redundant and defect\$3
(1266) (address near3 input) and (redundant with defect\$3)
(1170) ((address near3 input) and (redundant with defect\$3)) and
(198) (((address near3 input) and (redundant with defect\$3)) and
(31) (((address near3 input) and (redundant with defect\$3)) and
(144) ((address near2 input) near2 (circuit signal)) and redundant
(1) (defect\$3 near3 address) near3 stor\$3
(1) (defect\$3 with stor\$3) and redundan\$2
(7) defect\$3 with stor\$3
(1) (defect\$3 near3 address) and redundan\$2
(67880) memory and redundan\$2

DB: USPAT:USPGPUS:EPO:JPO:DERWENT:BM:ID8
Current OR
Current XRef
Retrieval C
Inventor
S C P X 3

U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	X	3
1		US 20030031058 A1	20030213	165	Semiconductor device formed in a rectangle region on a	365/189.09	257/E23.02; 365/51		Kajigaya, Kazuhiko et al.					
2		US 20020054514 A1	20020509	168	Semiconductor memory device and defect remedying method	365/189.02	257/E23.02		Kajigaya, Kazuhiko et al.					
3		US 6657901 B2	20031202	162	Semiconductor device formed in a rectangle region on a	365/189.02	257/E23.02; 365/51		Kajigaya, Kazuhiko et al.					
4		US 6515913 B2	20030204	160	Semiconductor memory device and defect remedying method	365/189.02	257/E23.02; 365/230.02		Kajigaya, Kazuhiko et al.					
5		US 6335884 B1	20020101	159	Semiconductor memory device and defect remedying method	365/189.02	257/E23.02; 365/230.02		Kajigaya, Kazuhiko et al.					
6		US 6212089 B1	20010403	161	Semiconductor memory device and defect remedying method	365/51	257/E23.02; 365/189.01		Kajigaya, Kazuhiko et al.					
7		US 6178127 B1	20010123	33	Semiconductor memory device allowing reliable repairing	365/200	365/230.03		Haraguchi, Yoshiyuki					
8		US 6160744 A	20001212	162	Semiconductor memory device and defect remedying method	365/200	365/189.02; 365/230.03		Kajigaya, Kazuhiko et al.					
9		US 6049500 A	20000411	160	Semiconductor memory device and defect remedying method	365/230.02	257/E23.02; 365/230.03		Kajigaya, Kazuhiko et al.					
10		US 5995422 A	19991130	10	Redundancy circuit and method of a semiconductor	365/200	365/225.7		Im, Heung-Soo et al.					
11		US 5854508 A	19981229	161	Semiconductor memory device having zigzag bonding pad	257/786	257/666; 257/784		Kajigaya, Kazuhiko et al.					
12		US 5602771 A	19970211	160	Semiconductor memory device and defect remedying method	365/51	257/E23.02; 365/230.03		Kajigaya, Kazuhiko et al.					

NO Details HTML

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